

Silicon Diffused Power Transistor

BU4506AZ

GENERAL DESCRIPTION

Enhanced performance, new generation, high-voltage, high-speed switching npn transistor in a plastic full-pack envelope intended for use in horizontal deflection circuits of colour television receivers. Features exceptional tolerance to base drive and collector current load variations resulting in a very low worst case dissipation.

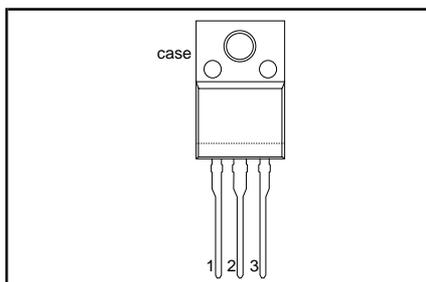
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0 V$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value		-	8	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25^\circ C$	-	32	W
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 3 A; I_B = 0.75 A$	-	3.0	V
I_{Csat}	Collector saturation current	$f = 16 kHz$	3.0	-	A
t_f	Fall time	$I_{Csat} = 3.0 A; f = 16 kHz$	300	450	ns

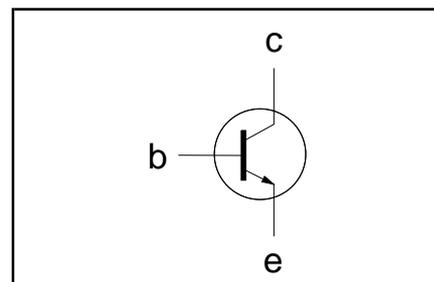
PINNING - SOT186A

PIN	DESCRIPTION
1	base
2	collector
3	emitter
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

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V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0 V$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value		-	8	A
I_B	Base current (DC)		-	3	A
I_{BM}	Base current peak value		-	5	A
$-I_{BM}$	Reverse base current peak value ¹		-	4	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25^\circ C$	-	32	W
T_{stg}	Storage temperature		-65	150	$^\circ C$
T_j	Junction temperature		-	150	$^\circ C$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th j-hs}$	Junction to heatsink	with heatsink compound	-	3.9	K/W
$R_{th j-a}$	Junction to ambient	in free air	55	-	K/W

¹ Turn-off current.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50\text{-}60\text{ Hz}$; sinusoidal waveform; $R.H. \leq 65\%$; clean and dustfree	-		2500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

STATIC CHARACTERISTICS

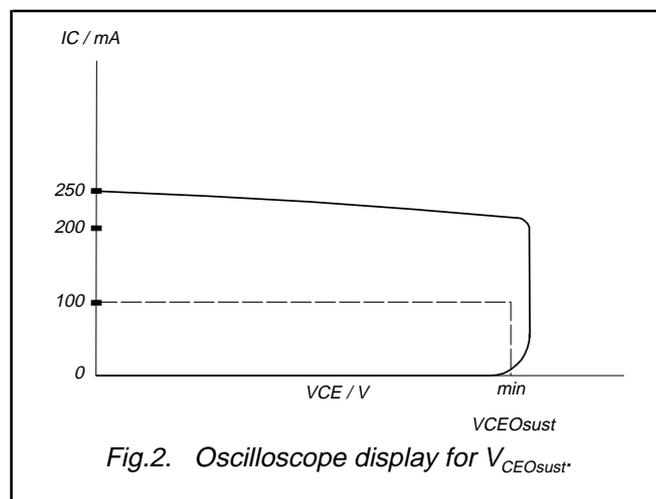
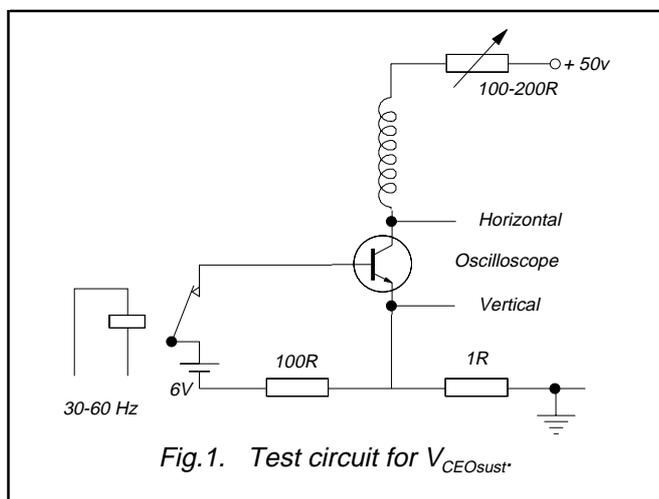
$T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current ²	$V_{BE} = 0\text{ V}$; $V_{CE} = V_{CESMmax}$	-	-	1.0	mA
I_{CES}		$V_{BE} = 0\text{ V}$; $V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	2.0	mA
BV_{EBO}	Emitter-base breakdown voltage	$I_B = 1\text{ mA}$	7.5	13.5	-	V
$V_{CEOsust}$	Collector-emitter sustaining voltage	$I_B = 0\text{ A}$; $I_C = 100\text{ mA}$; $L = 25\text{ mH}$	800	-	-	V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 3.0\text{ A}$; $I_B = 0.75\text{ A}$	-	-	3.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = 3.0\text{ A}$; $I_B = 0.75\text{ A}$	0.8	0.89	0.98	V
h_{FE}	DC current gain	$I_C = 0.5\text{ A}$; $V_{CE} = 5\text{ V}$	-	10	-	
h_{FE}		$I_C = 3\text{ A}$; $V_{CE} = 5\text{ V}$	4.2	5.5	7.3	

DYNAMIC CHARACTERISTICS

$T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

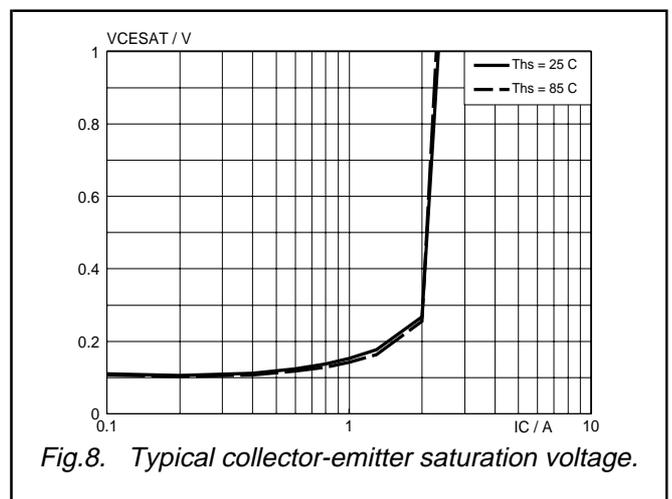
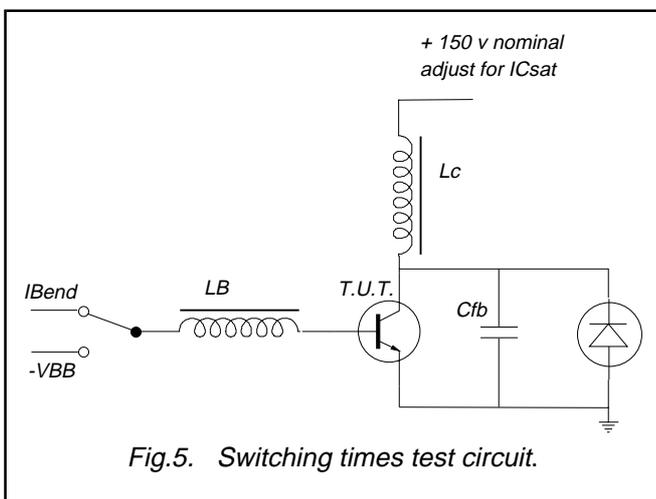
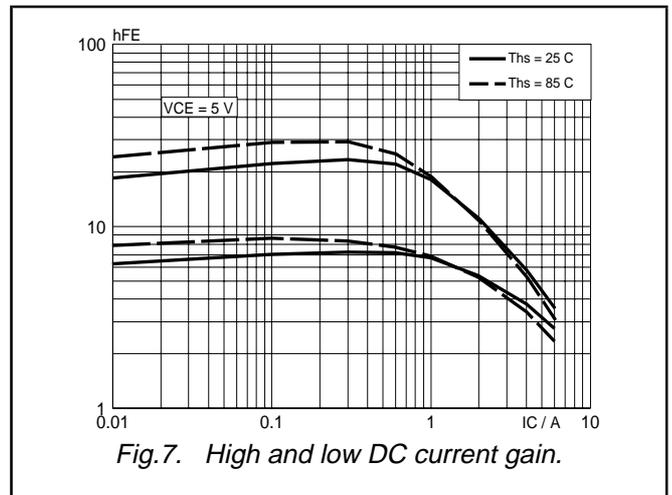
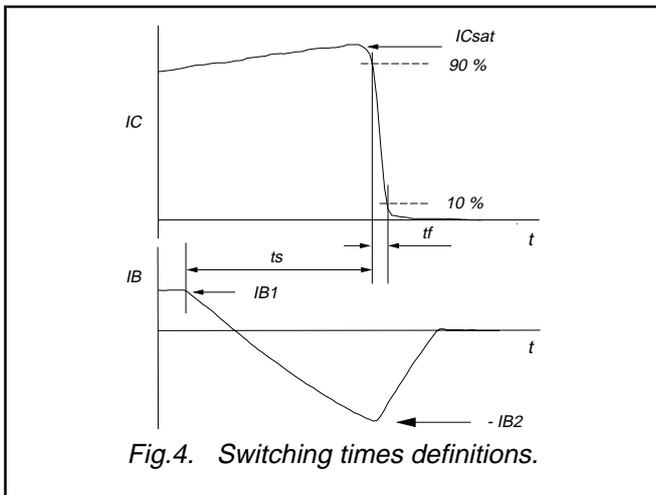
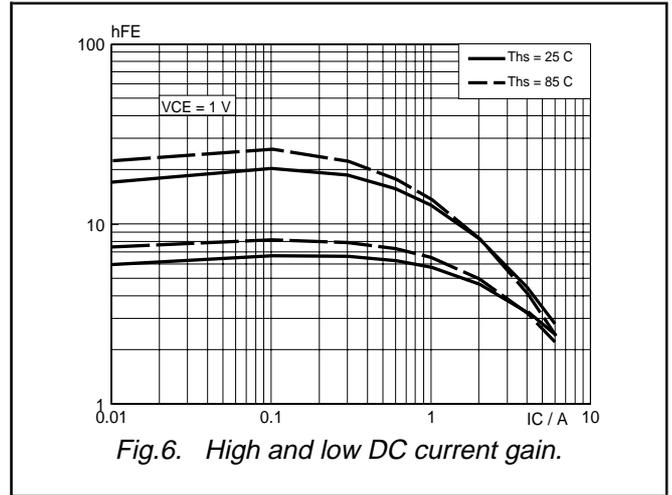
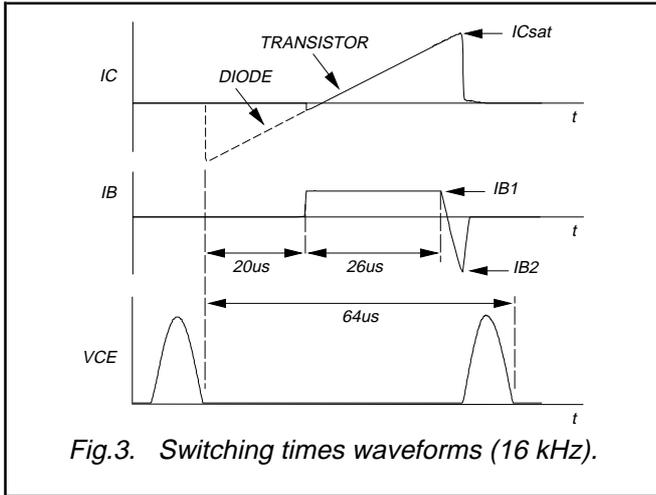
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
t_s	Switching times (16kHz line deflection circuit)	$I_{Csat} = 3.0\text{ A}$; $I_{B1} = 0.6\text{ A}$; ($I_{B2} = -1.5\text{ A}$)			
t_f	Turn-off storage time		3.7	4.6	μs
t_f	Turn-off fall time		300	450	ns



² Measured with half sine-wave voltage (curve tracer).

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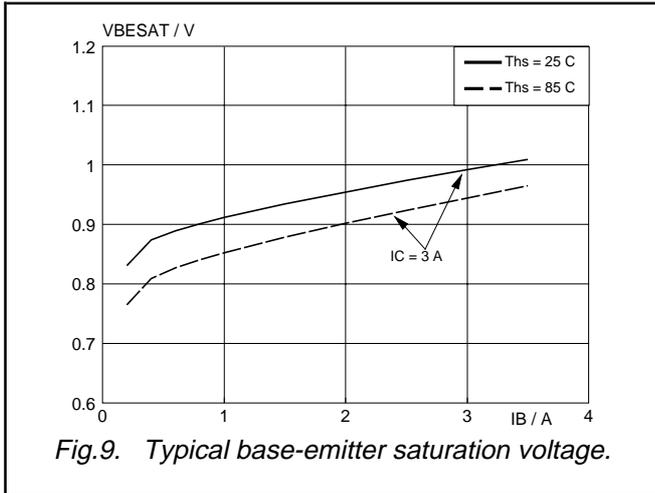


Fig.9. Typical base-emitter saturation voltage.

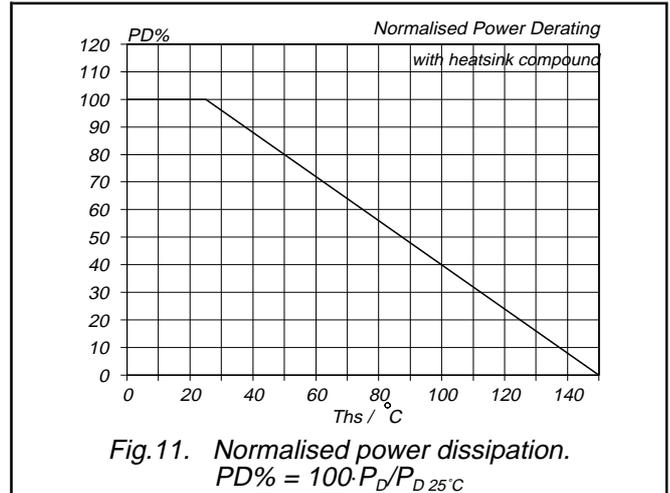


Fig.11. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D 25^\circ C}$

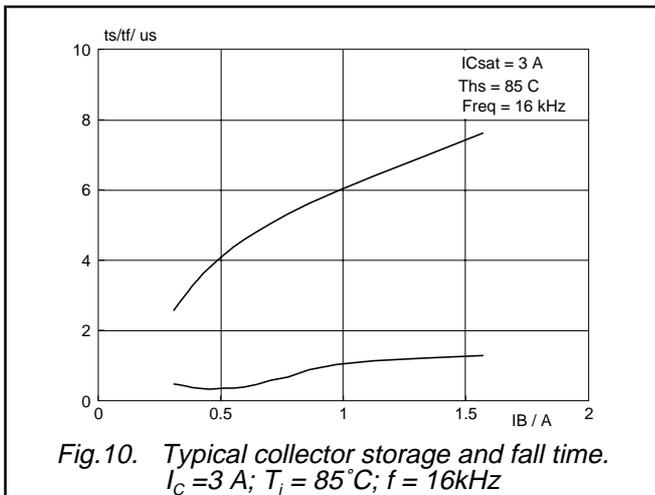


Fig.10. Typical collector storage and fall time.
 $I_C = 3 A; T_j = 85^\circ C; f = 16 kHz$

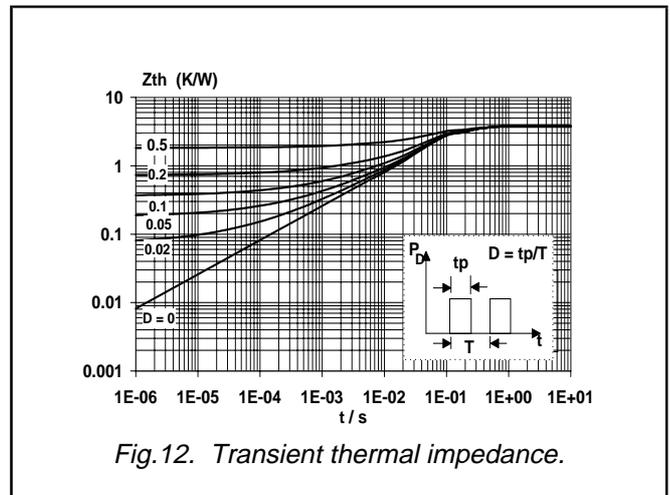


Fig.12. Transient thermal impedance.

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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